

P-channel TrenchMOS extremely low level FET Rev. 02 — 28 April 2010 Pr

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Extremely low level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

Low conduction losses due to low on-state resistance

### **1.3 Applications**

Battery management Load switching

### 1.4 Quick reference data

Table 1.	QUICK reference da	ita				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-	-20	V
I <sub>D</sub>	drain current	T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = -4.5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-7.9	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	5	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.8 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	40	50	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = -4.5 \; V; \; I_{D} = -4.7 \; A; \\ V_{DS} = -10 \; V; \; see \; \underline{Figure \; 11}; \\ see \; \underline{Figure \; 12} \end{array}$	-	1.3	-	nC

#### Table 1 Quick reference data



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## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source		
3	S	source		
4	G	gate		G_Ų┡┱Ţ
5	D	drain		
6	D	drain	SOT96-1 (SO8)	S 003aaa671
7	D	drain		
8	D	drain		

## 3. Ordering information

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
PMK50XP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		<b>JJ</b>				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-	-20	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 150 °C; R <sub>GS</sub> = 20 kΩ	-	-	-20	V
V <sub>GS</sub>	gate-source voltage		-12	-	12	V
I <sub>D</sub>	drain current	T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = -4.5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	-7.9	A
		T <sub>sp</sub> = 100 °C; V <sub>GS</sub> = -4.5 V; see <u>Figure 1</u>	-	-	-5	A
I <sub>DM</sub>	peak drain current	$T_{sp} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 3	-	-	-31.6	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	5	W
T <sub>stg</sub>	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
Source-drai	n diode					
Is	source current	T <sub>sp</sub> = 25 °C	-	-	-4.1	А
I <sub>SM</sub>	peak source current	$T_{sp} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed}$	-	-	-16.4	А

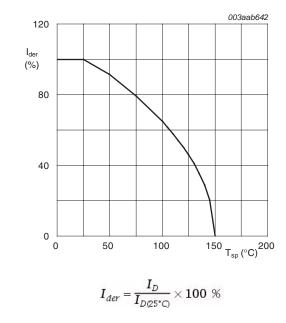
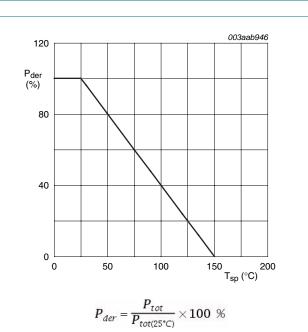


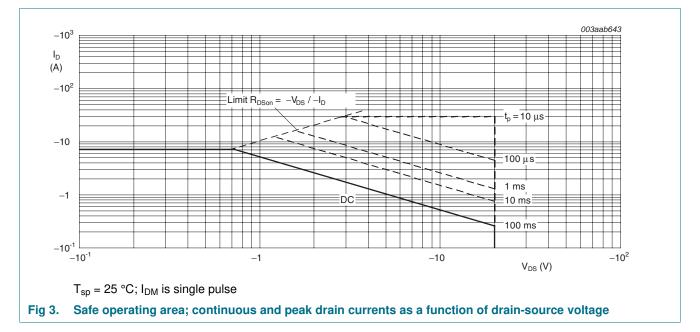
Fig 1. Normalized continuous drain current as a function of solder point temperature





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### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	see <u>Figure 4</u>	-	-	25	K/W

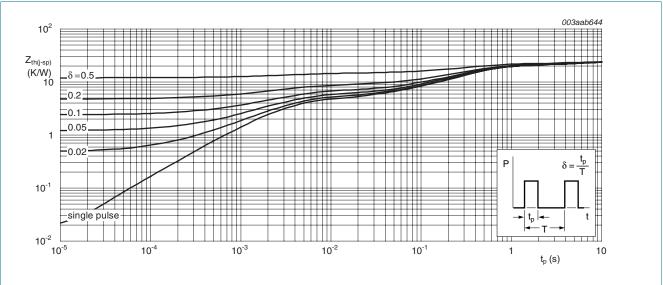


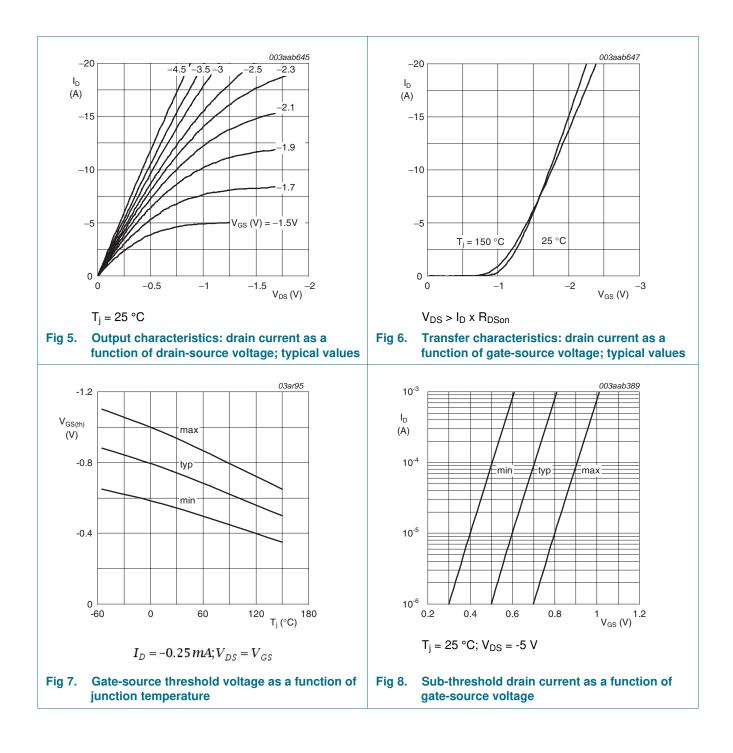
Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration

## 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-	aracteristics			71		
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	-18	-	-	V
	breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_i = 25 \ ^{\circ}\text{C}$	-20	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^\circ\text{C};$ see Figure 7; see Figure 8	-	-	-1.1	V
		$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-0.35	-	-	V
		$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 7</u> ; see <u>Figure 8</u>	-0.55	-0.75	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 70 °C	-	-	-5	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-10	-100	nA
	-	$V_{GS}$ = -12 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-10	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = -2.5 V; I <sub>D</sub> = -2.3 A; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	56	70	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -2.8 A; T <sub>j</sub> = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	64	80	mΩ
		V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -2.8 A; T <sub>j</sub> = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	40	50	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = -4.7 \text{ A}; V_{DS} = -10 \text{ V}; V_{GS} = -4.5 \text{ V};$	-	10	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 11;</u> see <u>Figure 12</u>	-	2.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	1.3	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D$ = -4.7 A; $V_{DS}$ = -10 V; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-1.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = -20 V; V_{GS} = 0 V; f = 1 MHz;$	-	1020	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	140	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	100	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $R_L$ = 10 $\Omega$ ; $V_{GS}$ = -4.5 V;	-	8.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$	-	7.5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	82	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.7 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see Figure 14	-	-0.77	-1.2	V

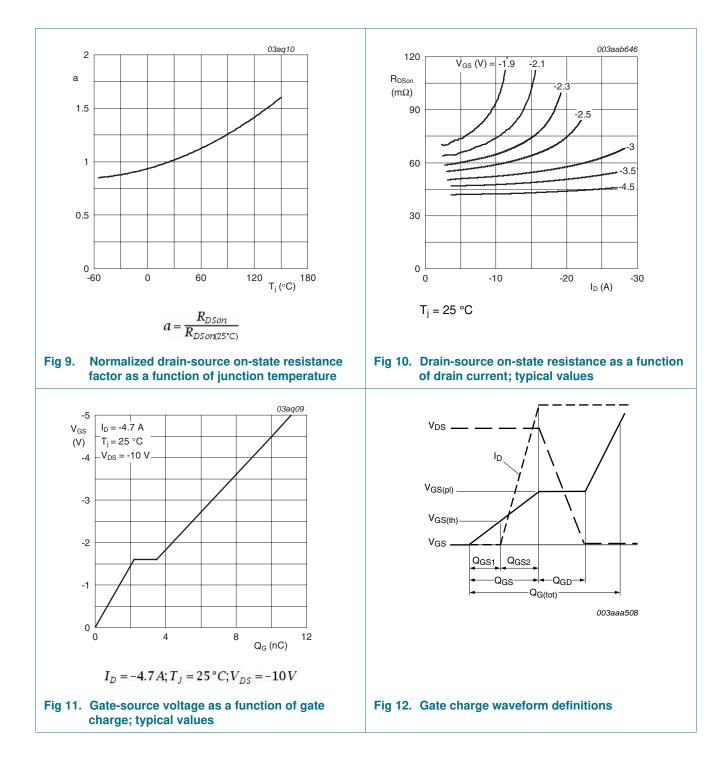
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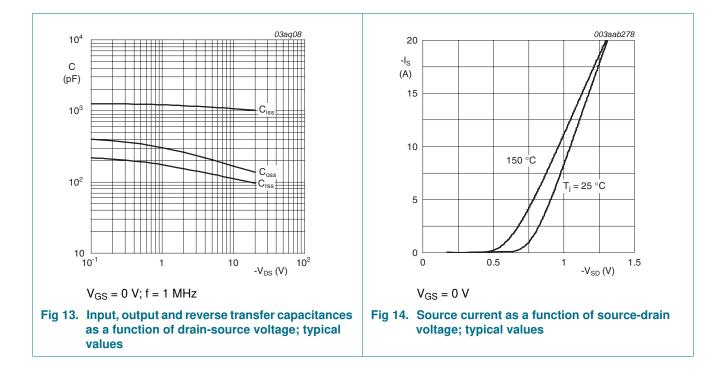
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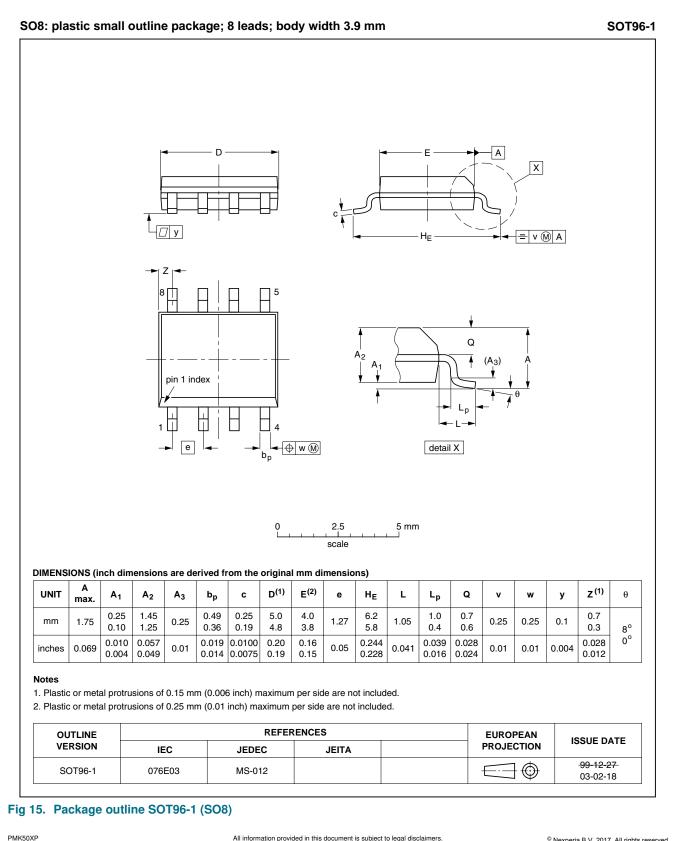


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#### **Package outline** 7.



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## 8. Revision history

Table 7. Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMK50XP_2	20100428	Product data sheet	-	PMK50XP_1
Modifications:	<ul> <li>Various cha</li> </ul>	anges to content.		
PMK50XP_1	20070917	Product data sheet	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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